



32M (2M x 16) SRAM

Features

- Very high speed: 70 ns
- Advanced low-power MoBL® architecture
- Wide voltage range:
 - V_{CC} range: 2.3V – 3.1V
 - V_{CCQ} range (I/O): 1.7V – V_{CC}
- Ultra-low active, standby power
- Easy memory expansion with \overline{CE} and \overline{OE} features
- 1T SRAM memory cell
- Automatic power-down when deselected
- CMOS for optimum speed/power

Functional Description^[1]

The MoBL3™ is a high-performance CMOS static RAM organized as 2M words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL) in portable applications such as cellular telephones. The device can be put into standby mode when deselected (\overline{CE} HIGH, or both BLE and BHE HIGH). The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected (\overline{CE} HIGH, or both BLE and BHE HIGH), outputs are disabled

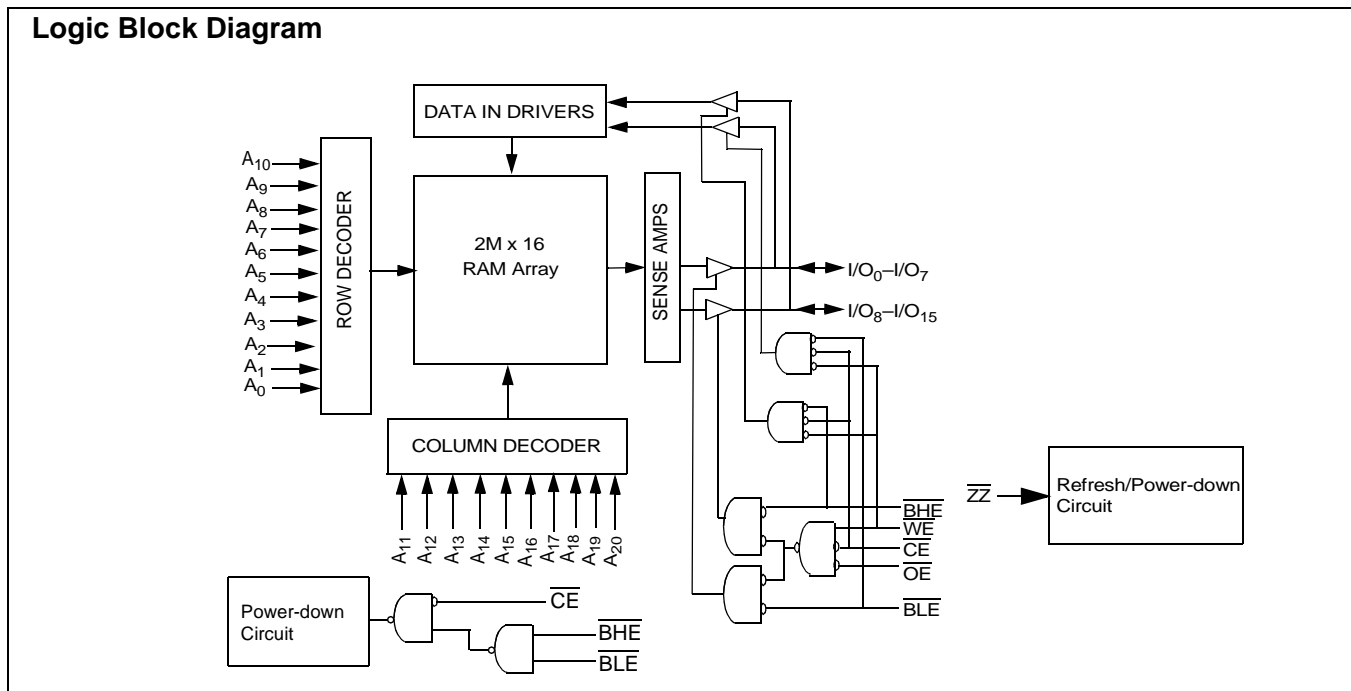
(\overline{OE} HIGH), or during a write operation (\overline{CE} LOW and \overline{WE} LOW).

Writing to the device is accomplished by taking Chip Enable (\overline{CE}) LOW and Write Enable (\overline{WE}) input LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₂₀). If Byte High Enable (\overline{BHE}) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₂₀).

Reading from the device is accomplished by taking Chip Enable (\overline{CE}) LOW and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable (\overline{BHE}) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this datasheet for a complete description of read and write modes.

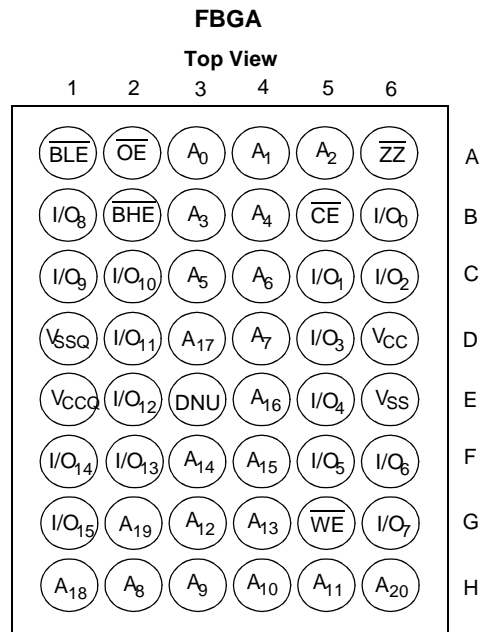
This SRAM has multiple power down functions. The \overline{ZZ} pin will put the SRAM into a deep sleep mode, where the data is not retained in the SRAM. The Variable Address Mode allows the user to retain data in a section of the SRAM and reduce the standby current. The CY81U032X16A7A has the deep sleep mode enabled on power-up. The VAR register can be used to disable the deep sleep mode.

The MoBL3 is available in a 48-ball FBGA package.



Note:

1. For best practice recommendations, please refer to the CY application note "System Design Guidelines" on <http://www.cypress.com>.

Pin Configuration^[2, 3]

Notes:

2. DNU pins are to be connected to V_{SS} or left open.
3. V_{SSQ} is the Ground pin for the I/O drivers. It should be connected to V_{SS}.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

- Storage Temperature -65°C to +150°C
- Ambient Temperature with Power Applied..... -55°C to +125°C
- Supply Voltage to Ground Potential-V25 -0.2V to +3.3V
- DC Voltage Applied to Outputs in High-Z State^[4, 5, 6] -0.2V to V_{CC} + 0.3V
- DC Input Voltage^[4, 5, 6] -0.2V to V_{CC} + 0.3V

- Output Current into Outputs (LOW)..... 20 mA
- Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)
- Latch-up Current..... > 200 mA

Operating Range

Ambient Temperature	V _{CC}	V _{CCQ}
-25°C to +85°C	2.3 to 3.1V	1.7V to V _{CC}

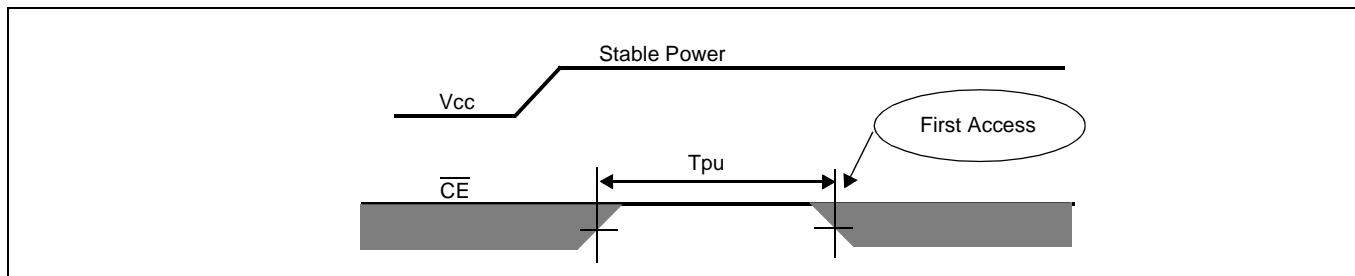
Product Portfolio

Product	V _{CC} Range			Cycle Time	t _{AA}	Power Dissipation					
						Operating (I _{CC})				Standby (I _{SB2})	
	Min.	Typ.	Max.			f = 1 MHz		f = f _{MAX}		Typ. ^[7]	Max.
						Typ. ^[7]	Max.	Typ. ^[7]	Max.		
CY81U032X16A7A-85	2.3V	2.5V	3.1V	85 ns	85 ns	2 mA			18 mA	100µA	
CY81U032X16A7A-70				70 ns	70 ns				21 mA		

Power-up Characteristics

The 32M needs to have a initialization time before accesses can be started on the device.

The initialization sequence is shown in the figure below. Chip Select (CE) should be HIGH for at least 200 us after V_{CC} has reached a stable value. No access must be attempted during this period of 200 us.



Parameter	Description	Min.	Typ.	Max.	Unit
T _{pu}	Chip Enable Low After Stable V _{CC}	200			µs

Note:

4. Overshoot: V_{CC} + 0.2V, pulse width < 20 ns.
5. Undershoot: -0.2V, pulse width < 20 ns.
6. Overshoot and undershoot specifications are characterized and are not 100% tested.
7. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.

Variable Address Refresh

Description

The variable address mode allows customers to turn off sections of the die to save standby current. The 32M MoBL3 is divided into four 8M sections allowing certain sections to be active (i.e., refreshed). The variable address mode also allows a customer to go into a low-power mode with \overline{ZZ} tied low and keep the data in a certain section of memory.

Function

At power up, all four sections of the die are activated and the SRAM enters into its default state of full memory size and refresh space.

MoBL3 provides three distinct operation modes for reducing standby power:

- Reduced Memory Size Operation
- Partial Array Refresh
- Deep Sleep Mode.

In the Reduced Memory Size (RMS) operation, the SRAM can be operated as a reduced size SRAM. For example, one could operate the 32M SRAM as an 8M, 16M, or a 32M memory block. The protocol to turn on/off the sections of the memory is given in the following pages. The RMS mode is enabled after \overline{ZZ} goes high and remains in RMS mode after \overline{ZZ} goes high.

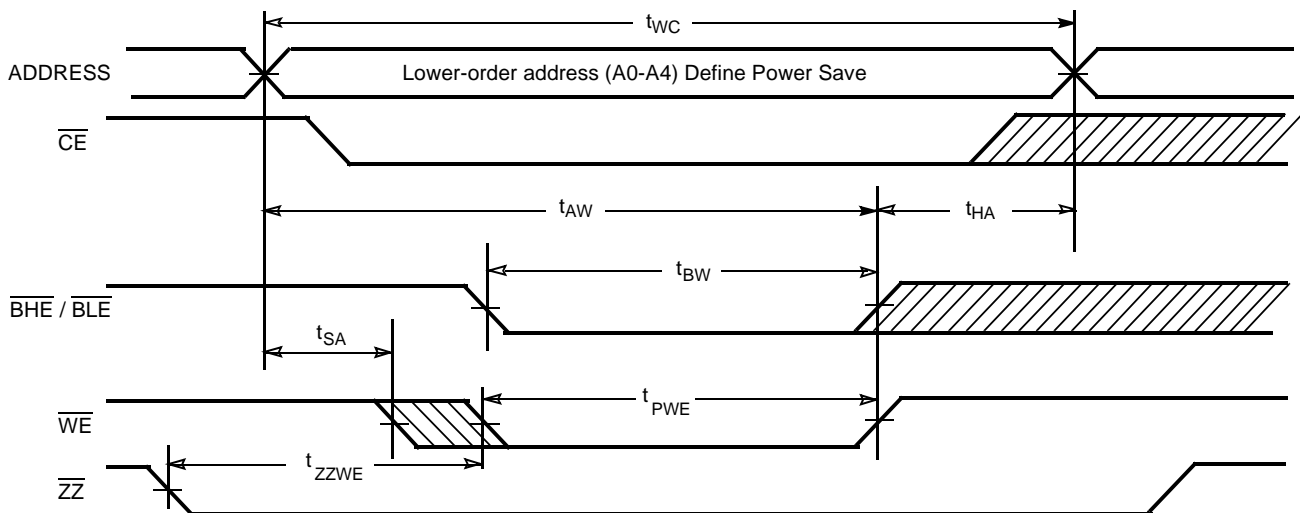
To revert back to a complete 32M SRAM, the protocol outlined on the next page will have to be followed, along with the bit pattern definitions shown on page 6.

In the Partial Array Refresh (PAR), the SRAM will only refresh certain portions of the memory, as configured by the user. This mode is only for standby and is applicable as long as \overline{ZZ} remains low. Once \overline{ZZ} returns high in this mode, the SRAM goes back to operating in full address refresh. The protocol shown on the next page will have to be followed to turn on/off this mode of operation. Once the Variable Address (VA) register is updated, all future PAR accesses will use the contents of the VA register when \overline{ZZ} returns low. If the customer wants to change the PAR space, the VA register must be updated per next figure.

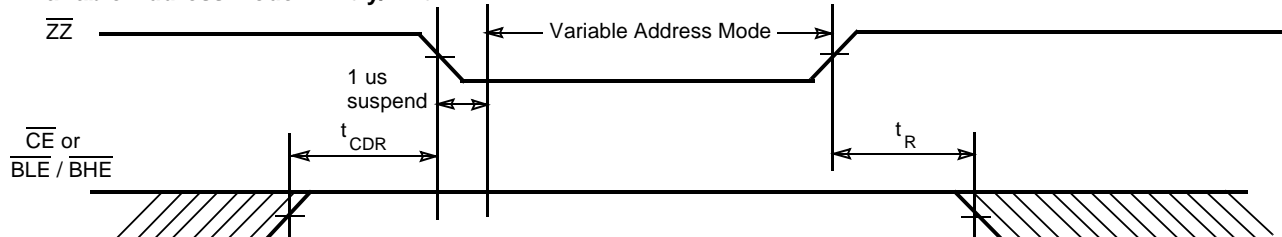
If the Variable Address (VA) register is not updated after power up, the SRAM will be in its default state. In the default state the whole memory array will be refreshed and driving \overline{ZZ} low places the SRAM into a deep sleep mode after 1us. Once in the deep sleep mode, data integrity in the SRAM is not guaranteed. If the customer updates the VA register, then address bit 4 (A4) must be set to 1, indicating to the SRAM that the deep sleep mode is disabled. At any point of time, one could drive \overline{ZZ} low and change the VA register's A4 bit back to 0. Then the SRAM enters deep sleep when \overline{ZZ} is driven low and remains in deep sleep mode until \overline{ZZ} is driven high. Once the SRAM enters into Deep Sleep Mode the content of the VA register is destroyed and the part returns to its default state.

Variable Address Refresh Switching Diagrams

Variable Address Mode—Register Update^[8]



Variable Address Mode—Entry/Exit

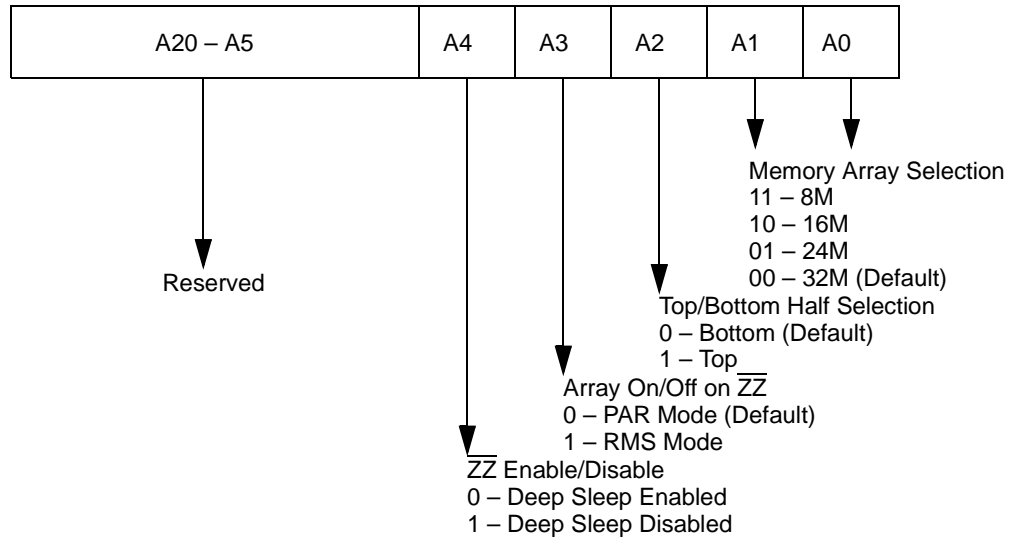


Note:

- \overline{OE} and the data pins are in a don't care state while the device is in variable address mode.

Variable Address Space Timings^[9]

Parameter	Description	Min.	Max.	Unit
t _{ZZWE}	ZZ LOW to WE LOW		1000	ns
t _{CDR}	Chip deselect to ZZ LOW	0		ns
t _R ^[10]	Operation Recovery Time (Deep Sleep Mode only)	200		μs
t _{ZZMIN}	Deep Sleep Mode Time	10		μs

Variable Address Space—Register

Variable Address Space—Address Patterns

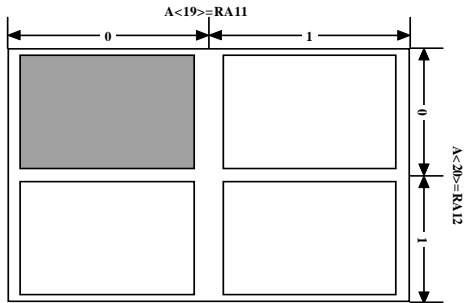
Partial Array Refresh Mode (A3=0, A4=1)					
A2	A1, A0	Refresh Section	Address	Size	Density
0	11	One-fourth of the Die	00000h – 07FFFFh (A20=A19=0)	512K x 16	8M
0	10	Half of the Die	00000h – 0FFFFFFh (A20=0, A19=0 or 1)	1M x 16	16M
0	01	Three-fourths of the Die	00000h – 17FFFFh (A20:A19 != 11)	1.5M x 16	24M
1	11	One-fourth of the Die	180000h – 1FFFFFFh (A20=A19=1)	512K x 16	8M
1	10	Half of the Die	100000h – 1FFFFFFh (A20=1, A19=0 or 1)	1M x 16	16M
1	01	Three-fourths of the Die	080000h – 1FFFFFFh (A20:A19 != 00)	1.5M x 16	24M
Reduced Memory Size Mode (A3=1, A4=1)					
0	11	One-fourth of the Die	00000h – 07FFFFh (A20=A19=0)	512K x 16	8M
0	10	Half of the Die	00000h – 0FFFFFFh (A20=0, A19=0 or 1)	1M x 16	16M
0	01	Three-fourths of the Die	00000h – 17FFFFh (A20:A19 != 11)	1.5M x 16	24M
0	00	Full Die	00000h – 1FFFFFFh	2M x 16	32M
1	11	One-fourth of the Die	180000h – 07FFFFh (A20=A19=0)	512K x 16	8M
1	10	Half of the Die	100000h – 0FFFFFFh (A20=0, A19=0 or 1)	1M x 16	16M
1	01	Three-fourths of the Die	080000h – 17FFFFh (A20:A19 != 00)	1.5M x 16	24M
1	00	Full Die	000000h – 1FFFFFFh	2M x 16	32M

Notes:

9. All other timing parameters are as shown in the data sheets.
10. t_R applies only in the deep sleep mode.

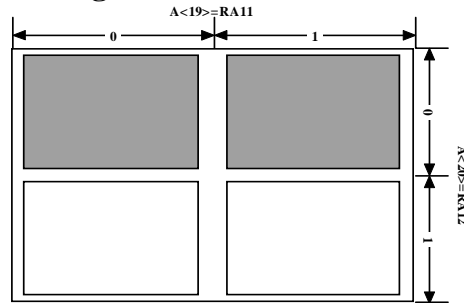
Memory Block Split

Bottom Address Range



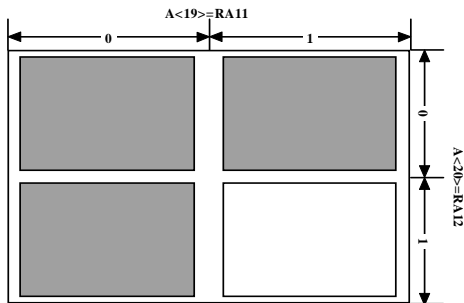
1/4 Address Space Refresh

Active Address Space:
A0-A18
A<19,20> = <0,0>



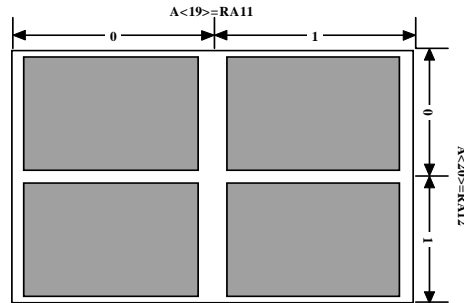
1/2 Address Space Refresh

Active Address Space:
A0-A19
A<20> = <0>



3/4 Address Space Refresh

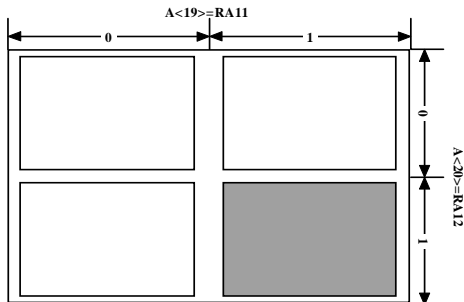
Active Address Space:
A0-A20
A<19,20> = <0,0>, <1,0>, <0,1>



Full Address Space Refresh

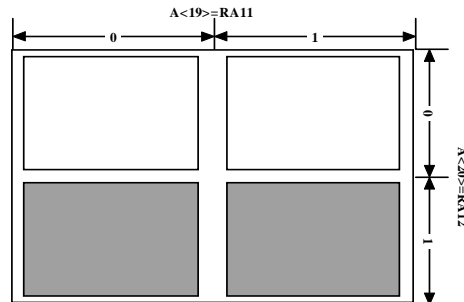
Active Address Space:
A0-A20
A<19,20> = <X,X>

Top Address Range



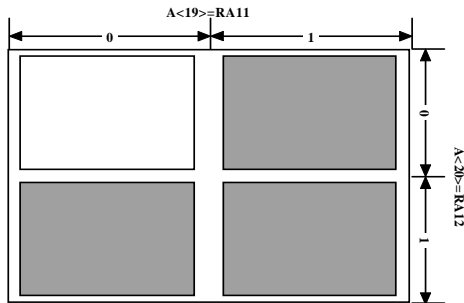
1/4 Address Space Refresh

Active Address Space:
A0-A18
A<19,20> = <1,1>



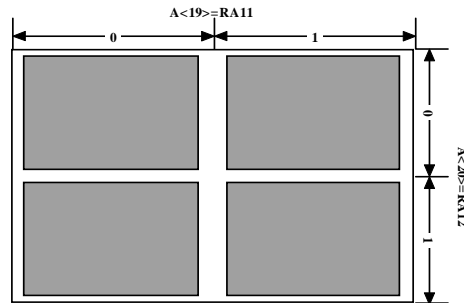
1/2 Address Space Refresh

Active Address Space:
A0-A19
A<20> = <1>



3/4 Address Space Refresh

Active Address Space:
A0-A20
A<19,20> = <1,0>, <0,1>, <1,1>



Full Address Space Refresh

Active Address Space:
A0-A20
A<19,20> = <X,X>

Electrical Characteristics Over the Operating Range^[4,5,6]

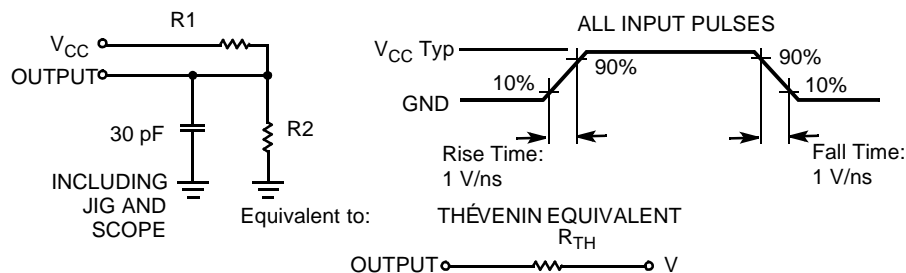
Parameter	Description	Test Conditions	CY81U032X16A7A			Unit
			Min.	Typ. ^[7]	Max.	
$V_{OH}^{[11]}$	Output HIGH Voltage	$I_{OH} = -0.1 \text{ mA}$	$V_{CCQ} - 0.2$			V
$V_{OL}^{[11]}$	Output LOW Voltage	$I_{OL} = 0.1 \text{ mA}$			0.2	V
$V_{IH}^{[12]}$	Input HIGH Voltage		1.4		$V_{CC} + 0.2V$	V
$V_{IL}^{[12]}$	Input LOW Voltage		-0.2		0.4	V
I_{IX}	Input Leakage Current	$GND \leq V_I \leq V_{CC}$	-1		+1	μA
I_{OZ}	Output Leakage Current	$GND \leq V_O \leq V_{CC}$, Output Disabled	-1		+1	μA
I_{CC}	V_{CC} Operating Supply Current	$I_{OUT} = 0 \text{ mA}$, $f = f_{MAX} = 1/t_{RC}$, $V_{CC} = \text{Max CMOS Levels}$		$t_{AA} = 85 \text{ ns}$	18	mA
				$t_{AA} = 70 \text{ ns}$	21	mA
		$I_{OUT} = 0 \text{ mA}$, $f = 1 \text{ MHz}$, CMOS Levels, $V_{CC} = \text{Max}$			2	mA
I_{SB1}	Automatic CE Power-down Current—CMOS Inputs	$CE \geq V_{CC} - 0.3V$ or $CE \leq 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, $f = f_{MAX}$ (Address and Data Only), $f=0$ (OE, WE, BHE, BLE) $V_{CC} = \text{Max}$			100	μA
I_{SB2}	Automatic CE Power-down Current—CMOS Inputs	$CE \geq V_{CC} - 0.3V$ or $CE \leq 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$, $f=0$, $V_{CC} = \text{Max}$			100	μA

Capacitance^[13]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	$T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{CC}(\text{typ})$	6	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance

Parameter	Description	Test Conditions	BGA	Unit
θ_{JA}	Thermal Resistance (Junction to Ambient) ^[13]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	55	$^\circ\text{C/W}$
θ_{JC}	Thermal Resistance (Junction to Case) ^[13]		16	$^\circ\text{C/W}$

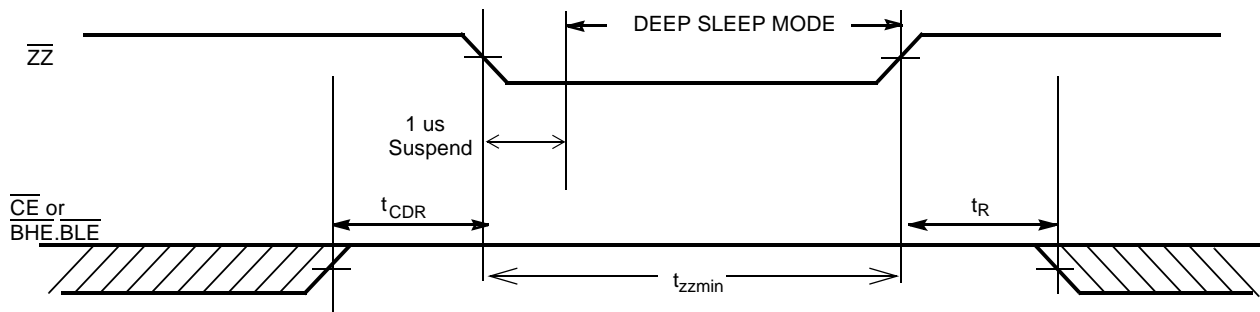
AC Test Loads and Waveforms

Notes:

- For $I_{OH} = -0.4 \text{ mA}$, $V_{OH} = 0.8 \times V_{CCQ}$; for $I_{OL} = 0.4 \text{ mA}$, $V_{OL} = 0.2 \times V_{CCQ}$.
- For $V_{CCQ} = 1.7 - 2.25V$: V_{IH} is higher of (1.4V, $0.8 \times V_{CCQ}$); V_{IL} is lower of (0.4V, $0.2 \times V_{CCQ}$).
- Tested initially and after any design or process changes that may affect these parameters.

Parameters	2.5V I/O	1.8V I/O	Unit
R1	21000	14000	Ohms
R2	21000	14000	Ohms
R _{TH}	10500	7000	Ohms
V _{TH}	1.25	0.9	Volts

Deep Sleep Mode^[14]

Parameter	Description	Conditions	Min.	Typ. ^[7]	Max.	Unit
I _{CCDS}	Deep Sleep Current	$\overline{CE} \geq V_{CC} - 0.2V$, $\overline{ZZ} \leq V_{IL}$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$ No input may exceed $V_{CC} + 0.2V$		7	10	μA
t _{CDR} ^[14]	Chip Deselect to Data Retention Time		0			ns
t _R	Operation Recovery Time		200			μs
t _{zzmin}	Deep Sleep mode Time		10			μs

Deep Sleep Waveform^[15]

Switching Characteristics Over the Operating Range^[16]

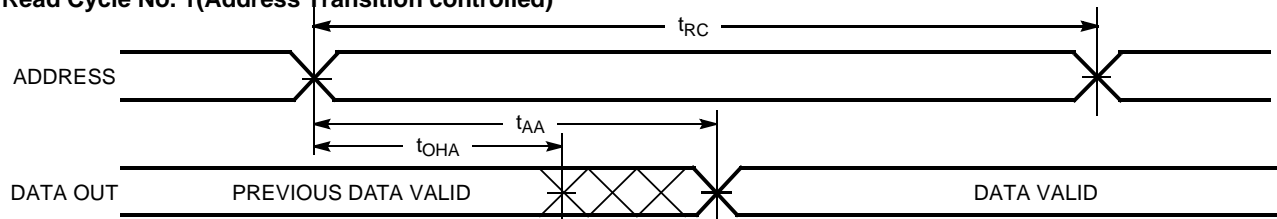
Parameter	Description	85 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t _{RC}	Read Cycle Time	85		70		ns
t _{AA}	Address to Data Valid		85		70	ns
t _{OHA}	Data Hold from Address Change	10		10		ns
t _{ACE}	CE LOW to Data Valid		85		70	ns
t _{DOE}	OE LOW to Data Valid		35		35	ns
t _{LZOE} ^[20]	OE LOW to Low-Z ^[17]	5		5		ns
t _{HZOE} ^[20]	OE HIGH to High-Z ^[17, 18]		25		25	ns
t _{LZCE} ^[20]	CE LOW to Low-Z ^[17]	10		10		ns
t _{HZCE} ^[20]	CE HIGH to High-Z ^[17, 18]		25		25	ns
t _{PU}	CE LOW to Power-up	0		0		ns
t _{PD}	CE HIGH to Power-down		85		70	ns
t _{DBE}	BLE / BHE LOW to Data Valid		85		70	ns
t _{LZBE} ^[20]	BLE / BHE LOW to Low-Z ^[17]	5		5		ns
t _{HZBE} ^[20]	BLE / BHE HIGH to High-Z ^[17, 18]		25		25	ns

Notes:

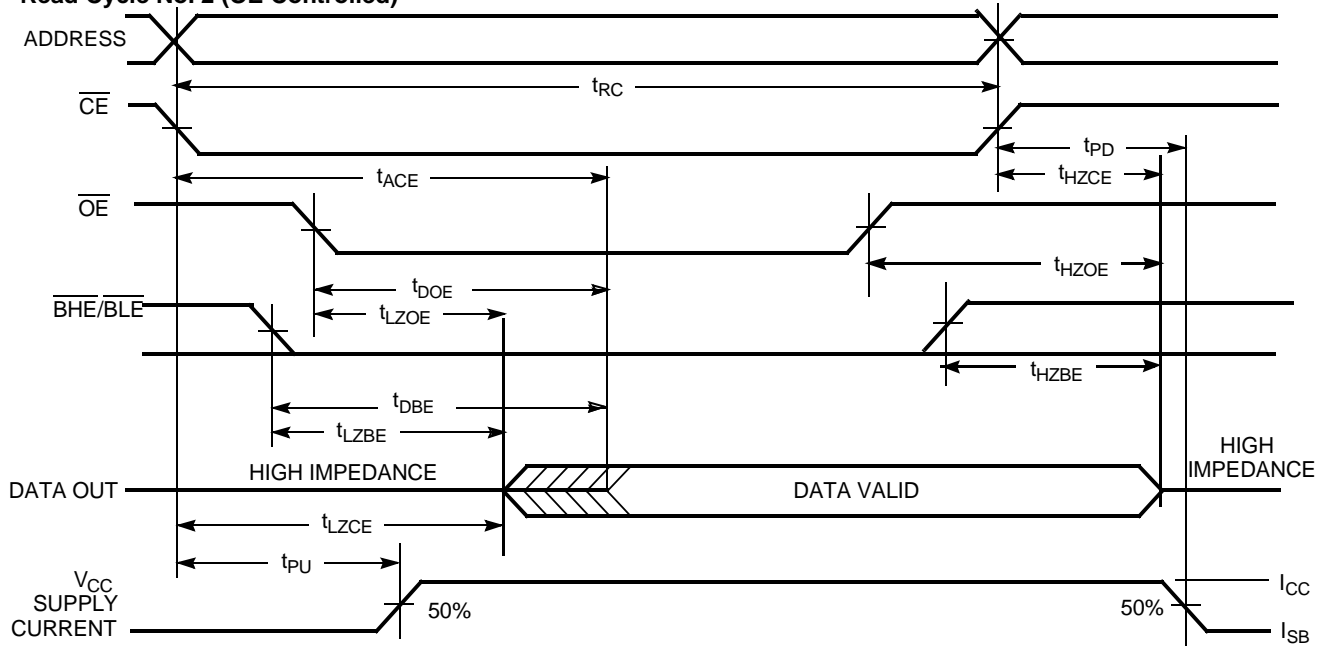
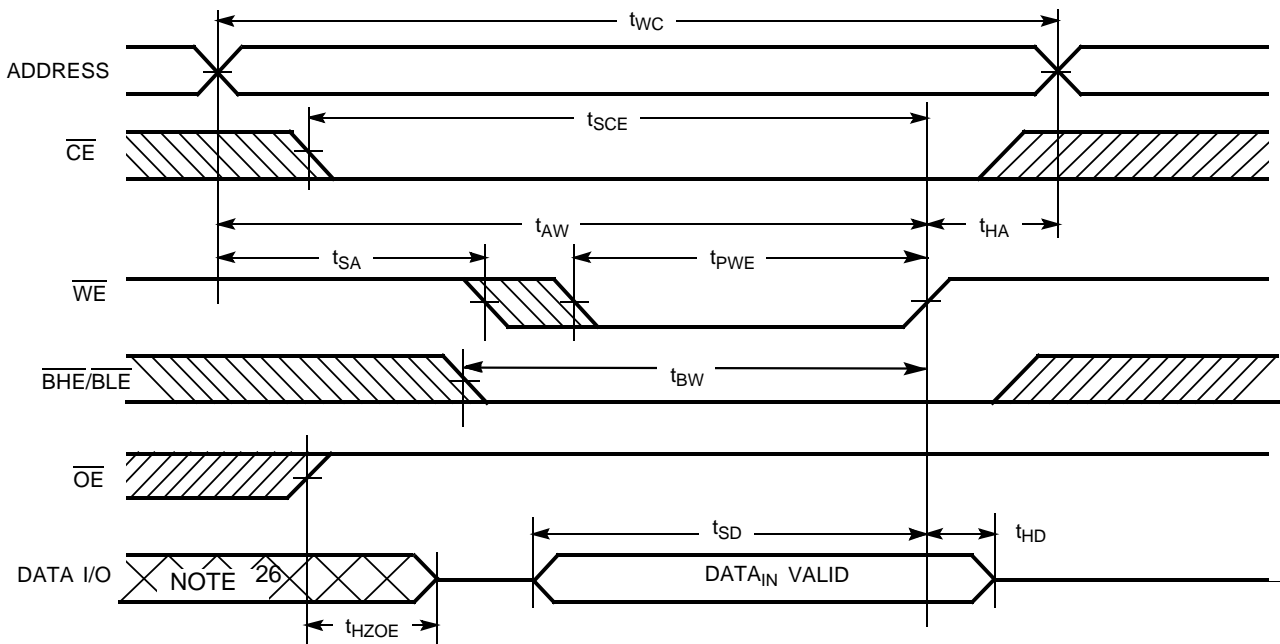
- This mode does not retain the data in the SRAM. All data will be lost in the mode of operation. This is the default mode of operation on the CY81U032X16A7A device.
- BHE.BLE is the AND of both BHE and BLE. Chip can be deselected by either disabling the chip enable signal (\overline{CE} HIGH) or by disabling both BHE and BLE (both HIGH).
- Test conditions assume signal transition time of 3ns or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.

Switching Characteristics Over the Operating Range^[16] (continued)

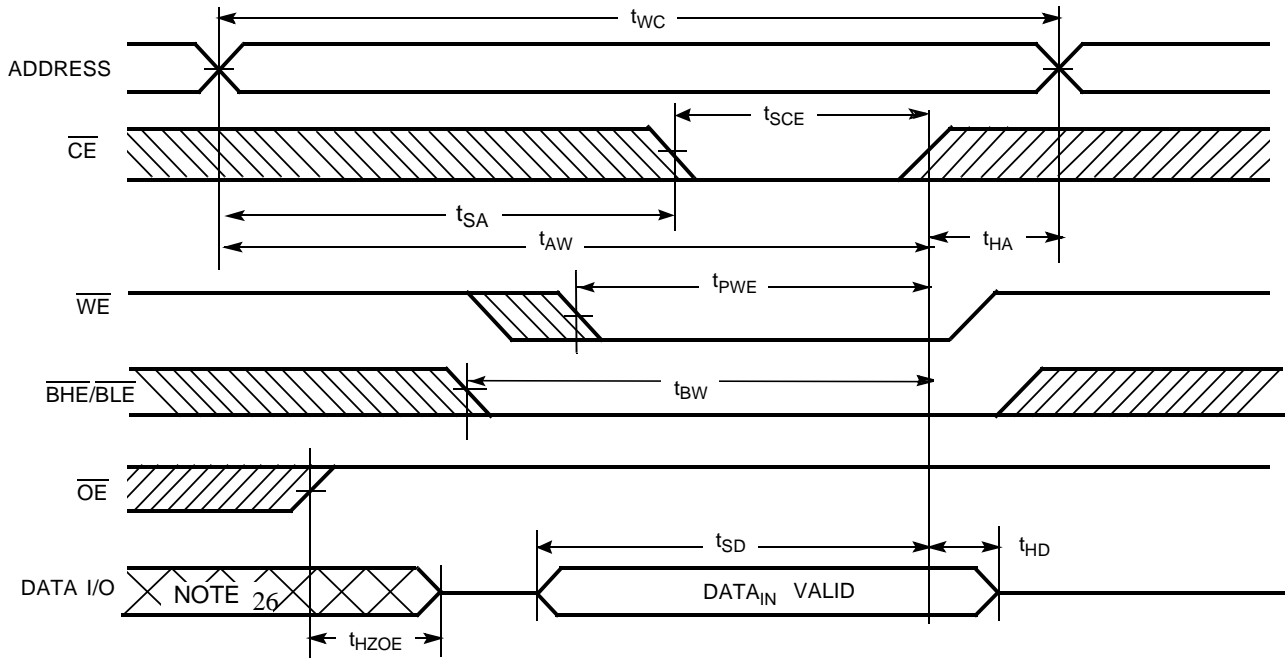
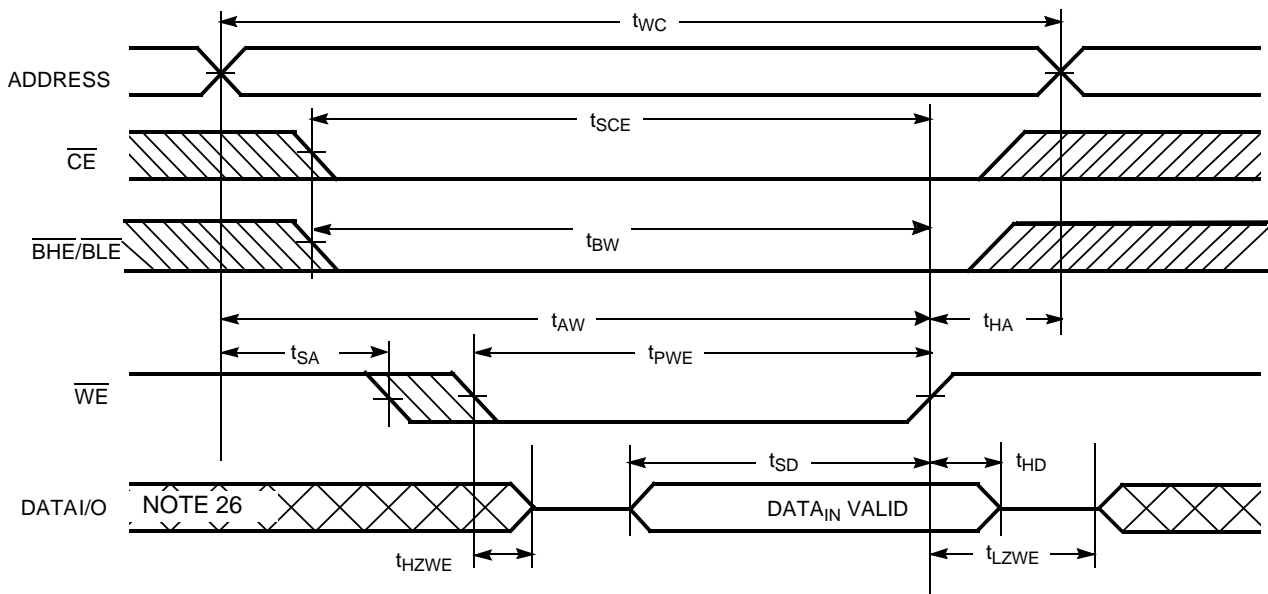
Parameter	Description	85 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Write Cycle^[19]						
t_{WC}	Write Cycle Time	85		70		ns
t_{SCE}	CE LOW to Write End	75		60		ns
t_{AW}	Address Set-up to Write End	75		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		ns
t_{PWE}	WE Pulse Width	65	1000	50	1000	ns
t_{BW}	BLE / BHE LOW to Write End	75		60		ns
t_{SD}	Data Set-up to Write End	30		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
$t_{HZWE}^{[20]}$	WE LOW to High-Z ^[17, 18]		25		25	ns
$t_{LZWE}^{[20]}$	WE HIGH to Low-Z ^[17]	10		10		ns

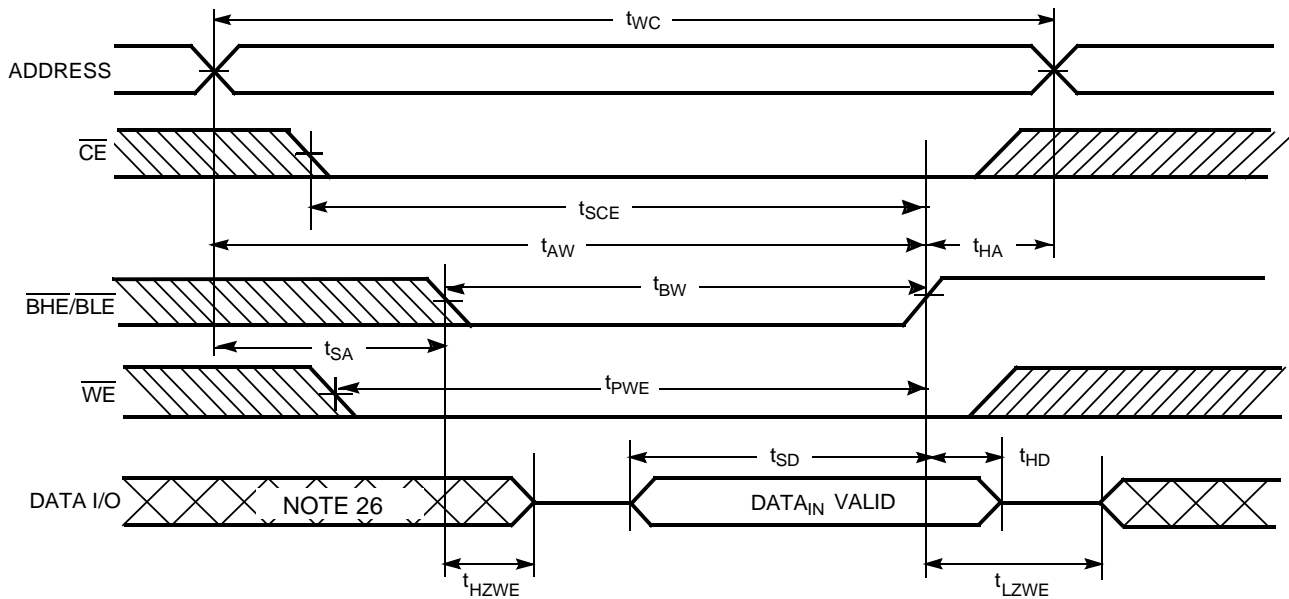
Switching Waveforms
Read Cycle No. 1 (Address Transition controlled)^[21, 22]

Notes:

17. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , t_{HZBE} is less than t_{LZBE} and t_{HZWE} is less than t_{LZWE} for any given device.
18. t_{HZOE} , t_{HZCE} , t_{HZBE} and t_{HZWE} transitions are measured when the output enters a high impedance state.
19. The internal write time of the memory is defined by the overlap of WE, CE = V_{IL} , BHE and/or BLE = V_{IL} . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.
20. High-Z and Low-Z parameters are guaranteed by design and are not tested.
21. Device is continuously selected. OE, CE = V_{IL} , BHE and/or BLE = V_{IL} .
22. WE is HIGH for read cycle.

Switching Waveforms (continued)
Read Cycle No. 2 (\overline{OE} Controlled) [22, 23]

Write Cycle No. 1 (\overline{WE} Controlled) [19, 24, 25]

Notes:

23. Address valid prior to or coincident with \overline{CE} transition LOW.
24. Data I/O is high impedance if $OE = V_{IH}$.
25. If \overline{CE} goes LOW simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.
26. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)
Write Cycle No. 2 (\overline{CE} Controlled) [19, 24, 25]

Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) [25]


Switching Waveforms (continued)
Write Cycle No. 4 (BHE/BLE Controlled, OE LOW) [25]

Truth Table

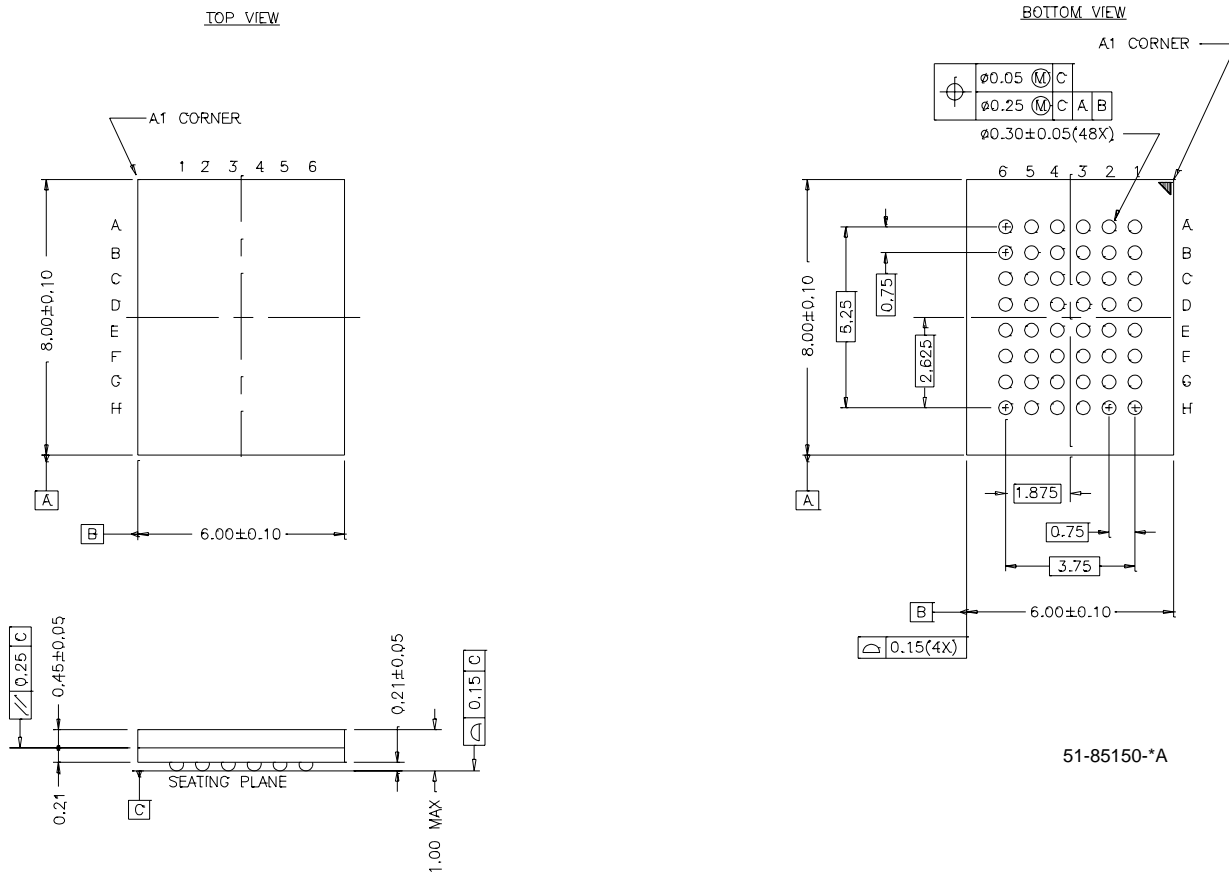
\overline{CE}	\overline{ZZ}	\overline{WE}	\overline{OE}	\overline{BHE}	\overline{BLE}	Inputs/Outputs	Mode	Power
X	H	X	X	H	H	High-Z	Deselect/Power-down	Standby (I_{SB})
H	H	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	X	X	High-Z	Deep Sleep Mode	Deep Sleep Current (I_{CCDS}) ^[27]
L	H	H	L	L	L	Data Out (I/O0–I/O15)	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O0–I/O7); High-Z (I/O8–I/O15)	Read	Active (I_{CC})
L	H	H	L	L	H	Data Out (I/O8–I/O15); High-Z (I/O0–I/O7)	Read	Active (I_{CC})
L	H	X	H	L	L	High-Z	Output Disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O0–I/O15)	Write	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O0–I/O7); High-Z (I/O8–I/O15)	Write	Active (I_{CC})
L	H	L	X	L	H	Data In (I/O8–I/O15); High-Z (I/O0–I/O7)	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
70	CY81U032X16A7A-7N4FI	BV48A	6 x 8 x 1 48-Ball Fine Pitch BGA	Industrial
85	CY81U032X16A7A-8N4FI			

Note:

27. This assumes that the deep sleep mode is enabled in the VAR register.

Package Diagrams
48-ball VFBGA (6 x 8 x 1 mm) BV48A


51-85150-*A

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PRELIMINARY

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